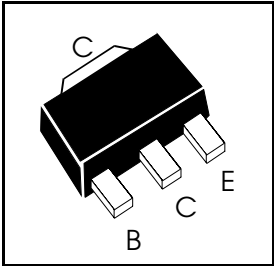


SOT89 PNP SILICON POWER
(SWITCHING) TRANSISTOR
ISSUE 1 - SEPTEMBER 1999

FCX1149A

FEATURES

- * **2W POWER DISSIPATION**
- * 20A Peak Pulse Current
- * Excellent H_{FE} Characteristics up to 10 Amps
- * Extremely Low Saturation Voltage E.g. 45mv Typ.
- * Extremely Low Equivalent On-resistance;
 $R_{CE(sat)}$ 67m Ω at 3A



Partmarking Detail - 149

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-30	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current **	I_{CM}	-10	A
Continuous Collector Current	I_C	-3	A
Base Current	I_B	-500	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	1 † 2 ‡	W W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

† recommended P_{tot} calculated using FR4 measuring 15x15x0.6mm

‡ Maximum power dissipation is calculated assuming that the device is mounted on FR4 substrate measuring 40x40x0.6mm and using comparable measurement methods adopted by other suppliers.

**Measured under pulsed conditions. Pulse width=300 μ s. Duty cycle $\leq$ 2%

Spice parameter data is available upon request for these devices.

Refer to the handling instructions for soldering surface mount components.

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ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	VALUE			UNIT	CONDITIONS.
		MIN.	TYP.	MAX.		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-30			V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	-25			V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-25			V	$I_C = -10\text{mA}^*$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEV}$	-25			V	$I_C = -100\mu\text{A}$, $V_{EB} = +1\text{V}$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}		-0.3	-100	nA	$V_{CB} = -24\text{V}$
Emitter Cut-Off Current	I_{EBO}		-0.3	-100	nA	$V_{EB} = -4\text{V}$
Collector Emitter Cut-Off Current	I_{CES}		-0.3	-100	nA	$V_{CES} = -20\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-45	-80	mV	$I_C = -0.1\text{A}$, $I_B = -1\text{mA}^*$
			-100	-170	mV	$I_C = -0.5\text{A}$, $I_B = -3\text{mA}^*$
			-140	-240	mV	$I_C = -1\text{A}$, $I_B = -7\text{mA}^*$
			-200	-300	mV	$I_C = -3\text{A}$, $I_B = -100\text{mA}^*$
			-230	-350	mV	$I_C = -4\text{A}$, $I_B = -140\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-930	-1050	mV	$I_C = -3\text{A}$, $I_B = -100\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-840	-1000	mV	$I_C = -3\text{A}$, $V_{CE} = -2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	270	450	800		$I_C = -10\text{mA}$, $V_{CE} = -2\text{V}^*$
		250	400			$I_C = -0.5\text{A}$, $V_{CE} = -2\text{V}^*$
		150	260			$I_C = -3.0\text{A}$, $V_{CE} = -2\text{V}^*$
		115	190			$I_C = -5.0\text{A}$, $V_{CE} = -2\text{V}^*$
			50			$I_C = -10.0\text{A}$, $V_{CE} = -2\text{V}^*$
Transition Frequency	f_T		135		MHz	$I_C = -50\text{mA}$, $V_{CE} = -10\text{V}$ $f = 50\text{MHz}$
Output Capacitance	C_{cb}		50		pF	$V_{CB} = -10\text{V}$, $f = 1\text{MHz}$
Switching Times	t_{on}		150		ns	$I_C = -4\text{A}$, $I_B = -40\text{mA}$, $V_{CC} = -10\text{V}$
	t_{off}		270		ns	$I_C = -4\text{A}$, $I_B = -40\text{mA}$, $V_{CC} = -10\text{V}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

TYPICAL CHARACTERISTICS

